Small Signal MOSFET

60 V, 115 mA, N-Channel SOT-23

Features

- 2V Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable (2V7002L)
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|-------------------------------------|---------------------|------------|
| Drain-Source Voltage | V _{DSS} | 60 | Vdc |
| Drain-Gate Voltage ($R_{GS} = 1.0 \text{ M}\Omega$) | V _{DGR} | 60 | Vdc |
| Drain Current - Continuous $T_C = 25^{\circ}C$ (Note 1) $T_C = 100^{\circ}C$ (Note 1) - Pulsed (Note 2) | I _D I _D | ±115 ±75 ±800 | mAdc |
| Gate-Source Voltage - Continuous - Non-repetitive (t _p ≤ 50 μs) | V _{GS} V _{GSM} | ±20 ±40 | Vdc Vpk |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------------------------|-------------------|---------------------|
| Total Device Dissipation FR-5 Board (Note 3) T _A = 25°C Derate above 25°C Thermal Resistance, Junction-to-Ambient | P_D | 225 1.8 556 | mW mW/°C °C/W |
| Total Device Dissipation (Note 4) Alumina Substrate, T _A = 25°C Derate above 25°C Thermal Resistance, Junction–to–Ambient | P _D | 300 2.4 417 | mW mW/°C °C/W |
| Junction and Storage Temperature | T _J , T _{stg} | -55 to +150 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

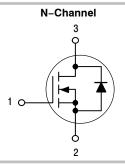
- The Power Dissipation of the package may result in a lower continuous drain current.
- 2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.
- 3. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 4. Alumina = 0.4 x 0.3 x 0.025 in 99.5% alumina.

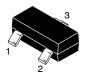


ON Semiconductor®

http://onsemi.com

| V _{(BR)DSS} | R _{DS(on)} MAX | I _D MAX |
|----------------------|-------------------------|--------------------|
| 60 V | 7.5 Ω @ 10 V, 500 mA | 115 mA |





DIAGRAM

MARKING

702 M=

SOT-23 CASE 318 STYLE 21

> 702 = Device Code M = Date Code* ■ Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or position may
vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping [†] | | |
|-------------|-----------|-----------------------|--|--|
| 2N7002LT1G | SOT-23 | 3000 Tape & Reel | | |
| 2N7002LT3G | (Pb-Free) | 10,000 Tape & Reel | | |
| 2V7002LT1G | | 3000 Tape & Reel | | |
| 2V7002LT3G | SOT-23 | 10,000 Tape & Reel | | |
| 2N7002LT1H* | (Pb-Free) | 3000 Tape & Reel | | |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}Not for new design.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

| Characteristic | Symbol | Min | Тур | Max | Unit | |
|--|----------------------|-------------|------------------|----------------------------|------|--|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage ($V_{GS} = 0$, $I_D = 10 \mu Adc$) | V _{(BR)DSS} | 60 | - | - | Vdc | |
| Zero Gate Voltage Drain Current $T_J = 25^{\circ}C$ $(V_{GS} = 0, V_{DS} = 60 \text{ Vdc})$ $T_J = 125^{\circ}C$ | | - | | 1.0 500 | μAdc | |
| Gate-Body Leakage Current, Forward (V _{GS} = 20 Vdc) | I _{GSSF} | _ | - | 100 | nAdc | |
| Gate-Body Leakage Current, Reverse (V _{GS} = -20 Vdc) | I _{GSSR} | - | - | -100 | nAdc | |
| ON CHARACTERISTICS (Note 5) | | | | | | |
| Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 250 μAdc) | V _{GS(th)} | 1.0 | - | 2.5 | Vdc | |
| On–State Drain Current $(V_{DS} \ge 2.0 V_{DS(on)}, V_{GS} = 10 \text{ Vdc})$ | I _{D(on)} | 500 | - | _ | mA | |
| Static Drain–Source On–State Voltage $(V_{GS} = 10 \text{ Vdc}, I_D = 500 \text{ mAdc})$ $(V_{GS} = 5.0 \text{ Vdc}, I_D = 50 \text{ mAdc})$ | V _{DS(on)} | - - | - - | 3.75 0.375 | Vdc | |
| $ \begin{array}{llllllllllllllllllllllllllllllllllll$ | ; | - - - | - - - - | 7.5 13.5 7.5 13.5 | Ohms | |
| Forward Transconductance ($V_{DS} \ge 2.0 V_{DS(on)}$, $I_D = 200 \text{ mAdc}$) | 9 _{FS} | 80 | - | _ | mS | |
| DYNAMIC CHARACTERISTICS | l | | I | | 1 | |
| Input Capacitance (V _{DS} = 25 Vdc, V _{GS} = 0, f = 1.0 MHz) | C _{iss} | - | _ | 50 | pF | |
| Output Capacitance (V _{DS} = 25 Vdc, V _{GS} = 0, f = 1.0 MHz) | C _{oss} | - | - | 25 | pF | |
| Reverse Transfer Capacitance (V _{DS} = 25 Vdc, V _{GS} = 0, f = 1.0 MHz) | C _{rss} | - | - | 5.0 | pF | |
| SWITCHING CHARACTERISTICS (Note 5) | <u>'</u> | | 1 | • | • | |
| Turn–On Delay Time $(V_{DD} = 25 \text{ Vdc}, I_D \approx 500 \text{ mAdc},$ | t _{d(on)} | - | - | 20 | ns | |
| Turn–Off Delay Time $R_G = 25 \Omega$, $R_L = 50 \Omega$, $V_{gen} = 10 V$) | t _{d(off)} | - | - | 40 | ns | |
| BODY-DRAIN DIODE RATINGS | | | | | | |
| Diode Forward On-Voltage (I _S = 11.5 mAdc, V _{GS} = 0 V) | V _{SD} | _ | - | -1.5 | Vdc | |
| Source Current Continuous (Body Diode) | I _S | _ | - | -115 | mAdc | |
| Source Current Pulsed | I _{SM} | - | - | -800 | mAdc | |
| | • | | | | | |

^{5.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

TYPICAL ELECTRICAL CHARACTERISTICS

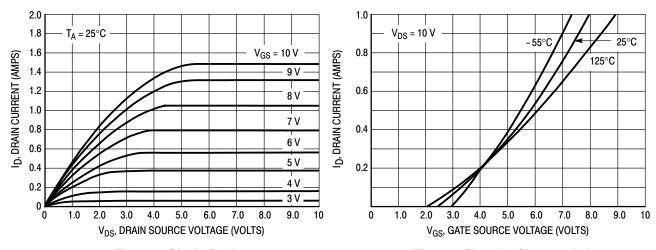


Figure 1. Ohmic Region

Figure 2. Transfer Characteristics

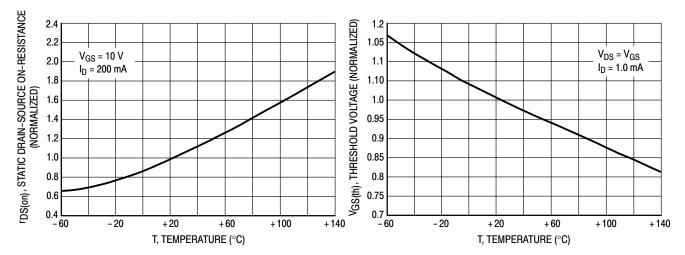
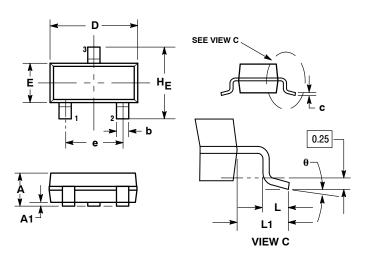


Figure 3. Temperature versus Static Drain-Source On-Resistance

Figure 4. Temperature versus Gate Threshold Voltage

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP**



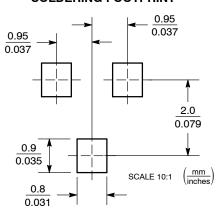
NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|--------|-------|-------|
| DIM | MIN | NOM | MAX | MIN | NOM | MAX |
| Α | 0.89 | 1.00 | 1.11 | 0.035 | 0.040 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.001 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.018 | 0.020 |
| С | 0.09 | 0.13 | 0.18 | 0.003 | 0.005 | 0.007 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| е | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.081 |
| L | 0.10 | 0.20 | 0.30 | 0.004 | 0.008 | 0.012 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.029 |
| HE | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| θ | 0° | | 10° | 0° | | 10° |

STYLE 21:

- PIN 1. GATE SOURCE
 - 2. 3. DRAIN
- **SOLDERING FOOTPRINT**



ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking, tadefined to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Literature Distribution Center for ON Semiconductor

P.O. Box 5163, Denver, Colorado 80217 USA **Phone**: 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax**: 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor:

2N7002LT1G 2N7002LT3G 2V7002LT1G 2V7002LT3G